

Listing of Claims:

This listing of claims will replace all prior versions, and listing, of claims in the application:

Claim 1 (original): Apparatus, comprising:

- a) first and second mounds of dielectric, respectively encapsulating first and second conductors;
- b) a third dielectric, filling a valley between the first and second mounds of dielectric, and encapsulating a third conductor; and
- c) a first ground shield deposited on at least sides of the first and second mounds of dielectric, abutting the third dielectric.

Claim 2 (original): The apparatus of claim 1, further comprising a second ground shield on which the first and second mounds of dielectric are deposited; wherein the first ground shield extends to the second ground shield.

Claim 3 (original): The apparatus of claim 2, further comprising a third ground shield deposited on the third dielectric; the third ground shield contacting the first ground shield.

Claim 4 (previously presented): The apparatus of claim 1, wherein the first and second mounds of dielectric, and the third dielectric, are glass dielectrics.

Claim 5 (previously presented): The apparatus of claim 1, wherein the first and second mounds of dielectric, and the third dielectric, are ceramic dielectrics.

Claim 6 (previously presented): The apparatus of claim 1, wherein the first and second mounds of dielectric, and the third dielectric, are KQ CL-90-7858 dielectrics.

Claim 7 (previously presented): The apparatus of claim 1, wherein the first and second mounds of dielectric, and the third dielectric, are thickfilm dielectrics.

Claim 8 (previously presented): A method for forming shielded transmission lines, comprising:

- a) depositing first and second lower mounds of dielectric on a first ground shield;
- b) depositing conductors on the first and second lower mounds of dielectric;
- c) depositing first and second upper mounds of dielectric on the first and second lower mounds of dielectric;
- d) depositing a second ground shield over the first and second upper and lower mounds of dielectric;
- e) depositing a third lower dielectric in a valley between the first and second upper and lower mounds of dielectric;
- f) depositing a conductor on the third lower dielectric;
- g) depositing a third upper dielectric on the third lower dielectric; and
- h) depositing a third ground shield over the third upper dielectric.

Claim 9 (previously presented): The method of claim 8, wherein the first and second upper and lower mounds of dielectric, and the third upper and lower dielectrics, are glass dielectrics.

Claim 10 (previously presented): The method of claim 8, wherein the first and second upper and lower mounds of dielectric, and the third upper and lower dielectrics, are ceramic dielectrics.

Claim 11 (previously presented): The method of claim 8, wherein the first and second upper and lower mounds of dielectric, and the third upper and lower dielectrics, are KQ CL-90-7858 dielectrics.

Claim 12 (previously presented): The method of claim 8, wherein the first and second upper and lower mounds of dielectric, and the third upper and lower dielectrics, are thickfilm dielectrics.

Claim 13 (previously presented): A method for forming shielded transmission lines, comprising:

- a) depositing first and second lower mounds of dielectric on a first ground shield;
- b) depositing ground shield walls on sides of the first and second lower mounds of dielectric;
- c) depositing a third lower dielectric in a valley between the first and second lower mounds of dielectric;
- d) depositing conductors on each of the lower mounds of dielectric;
- e) depositing first and second upper mounds of dielectric on the first and second lower mounds of dielectric, respectively;
- f) depositing ground shield caps over the first and second upper mounds of dielectric, respectively;
- g) depositing a third upper dielectric on the third lower dielectric; and
- h) depositing a second ground shield over the third upper dielectric.

Claim 14 (previously presented): The method of claim 13, wherein the first and second upper and lower mounds of dielectric, and the third upper and lower dielectrics, are glass dielectrics.

Claim 15 (previously presented): The method of claim 13, wherein the first and second upper and lower mounds of dielectric, and the third upper and lower dielectrics, are ceramic dielectrics.

Claim 16 (previously presented): The method of claim 13, wherein the first and second upper and lower mounds of dielectric, and the third upper and lower dielectrics, are KQ CL-90-7858 dielectrics.

Claim 17 (original): The method of claim 13, further comprising polishing the lower dielectrics prior to depositing the conductors.

Claim 18 (previously presented): The method of claim 13, wherein each of the first and second upper and lower mounds of dielectric, and the third upper and lower dielectrics, is deposited by printing multiple layers of thickfilm dielectric and then firing the layers.

Claim 19 (original): The method of claim 18, further comprising polishing the lower dielectrics prior to depositing the conductors.

Claim 20 (original): The method of claim 13, wherein the height of the third lower dielectric is less than the heights of the first and second lower mounds of dielectric.